SAMTM data sheet SAM-810-5-1ps-x, λ = 810 nm

 $\lambda = 810 \text{ nm}$ Laser wavelength

High reflection band (R > 90%) λ = 785 .. 830 nm

Absorbance $A_0 = 5 \%$ Modulation depth $\Delta R = 3 \%$ Non-saturable loss $A_{ns} = 2 \%$

 $\Phi_{\text{sat}} = 110 \, \mu \text{J/cm}^2$ Saturation fluence

Relaxation time constant $\tau \sim 1 \text{ ps}$

 $\Phi_{\text{sat}} = 2 \text{ mJ/cm}^2$ Damage threshold

Chip area 4mm x 4mm; other dimensions on request

Chip thickness 450 µm

Protection the SAM is protected with a dielectric front layer

Mounting option **x** denotes the type of mounting as follows:

 $\mathbf{x} = 0$ unmounted glued on a gold plated Cu-cylinder with 12.7 mm \varnothing x = 12.7 gx = 25.4 gglued on a gold plated Cu-cylinder with 25.4 mm Ø soldered on a gold plated Cu-cylinder with 12.7 mm \varnothing x = 12.7 ssoldered on a gold plated Cu-cylinder with 25.4 mm \varnothing x = 25.4 sx = 25.0 wsoldered on a water cooled Cu-cylinder with 25.0 mm Ø x = FCmounted on a 1 m monomode fiber cable with FC connector

Low intensity spectral reflectance

